



### CST60P03 P-Ch 30V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

#### CST60P03 Product Summary



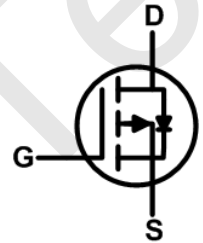
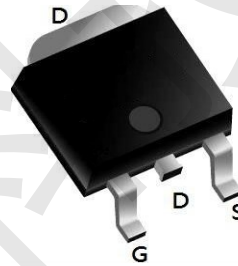
BVDSS	RDSON	ID
-30V	7.5mΩ	-60A

#### CST60P03 Description

The CST60P03 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The CST60P03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### CST60P03 TO252 Pin Configuration



#### CST60P03 Absolute Maximum Ratings (T<sub>A</sub> = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	-30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	-60	A
	T <sub>C</sub> =100°C		-32	
Pulsed Drain Current <sup>1</sup>		I <sub>DM</sub>	-200	A
Single Pulse Avalanche Energy <sup>2</sup>		EAS	80	mJ
Total Power Dissipation	T <sub>C</sub> =25°C	P <sub>D</sub>	43.1	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

#### Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>3</sup>	R <sub>θJA</sub>	70	°C/W
Thermal Resistance from Junction-to-Case	R <sub>θJC</sub>	2.9	°C/W



### CST60P03 P-Ch 30V Fast Switching MOSFETs

#### CST60P03 Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Static Characteristics</b>							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30	-	-	V	
Gate-body Leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	T <sub>J</sub> =25°C	-	-	-1	μA
			T <sub>J</sub> =100°C	-	-	-100	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.5	-2.5	V	
Drain-Source on-Resistance <sup>4</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -15A	-	7.5	14	mΩ	
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A	-	10.5	22		
Forward Transconductance <sup>4</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -15A	-	44	-	S	
<b>Dynamic Characteristics<sup>5</sup></b>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz	-	2503	-	pF	
Output Capacitance	C <sub>oss</sub>		-	315	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	279	-		
Gate Resistance	R <sub>g</sub>	f = 1MHz	-	10.5	-	Ω	
<b>Switching Characteristics<sup>5</sup></b>							
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V, I <sub>D</sub> = -15A	-	30	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	5	-		
Gate-Drain Charge	Q <sub>gd</sub>		-	7.5	-		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -15V, R <sub>G</sub> = 2.5Ω, I <sub>D</sub> = -15A	-	14.1	-	ns	
Rise Time	t <sub>r</sub>		-	20	-		
Turn-off Delay Time	t <sub>d(off)</sub>		-	94	-		
Fall Time	t <sub>f</sub>		-	65	-		
<b>Drain-Source Body Diode Characteristics</b>							
Diode Forward Voltage <sup>4</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	-	-	-1.2	V	
Continuous Source Current	I <sub>S</sub>	T <sub>C</sub> =25°C	-	-	-60	A	

#### Notes:

1. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
2. The EAS data shows Max. rating . The test condition is V<sub>DD</sub>= -25V, L=0.1mH, I<sub>AS</sub>= -40A.



CST60P03 Typical Characteristics

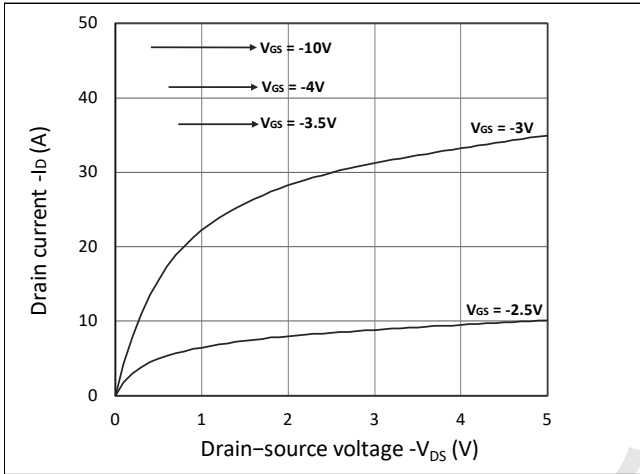


Figure 1. Output Characteristics

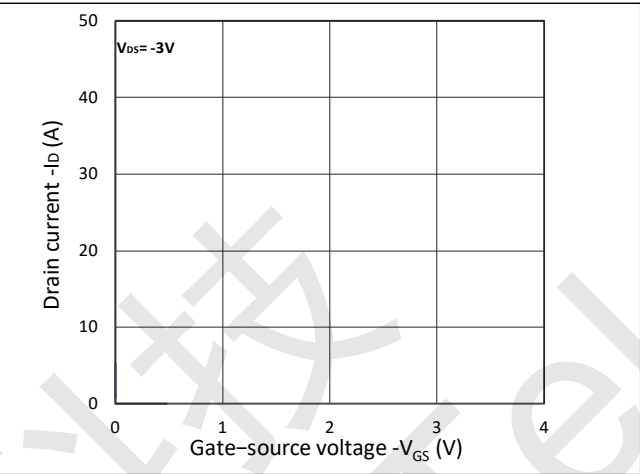


Figure 2. Transfer Characteristics

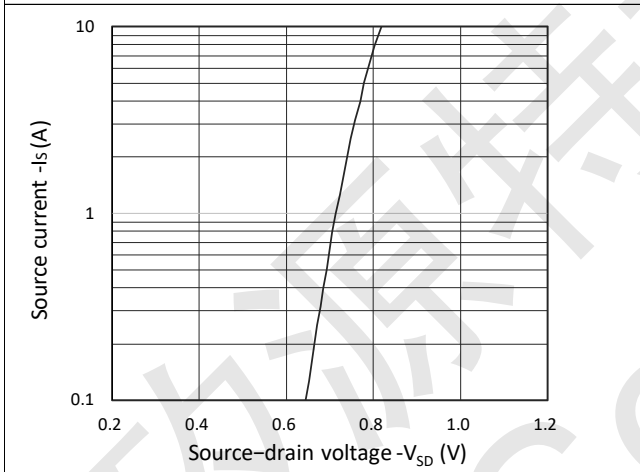


Figure 3. Forward Characteristics of Reverse

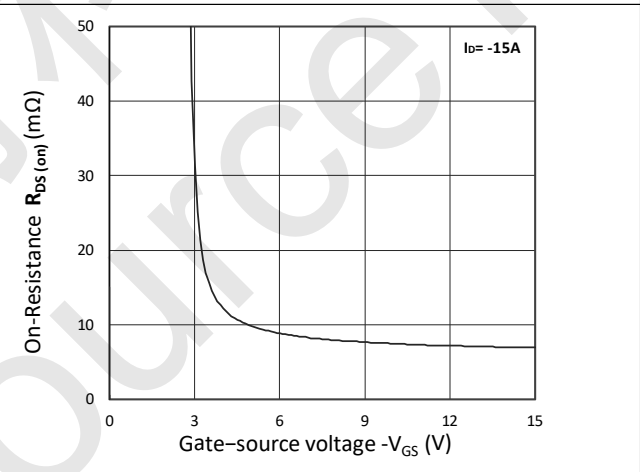


Figure 4.  $R_{DS(ON)}$  vs.  $V_{GS}$

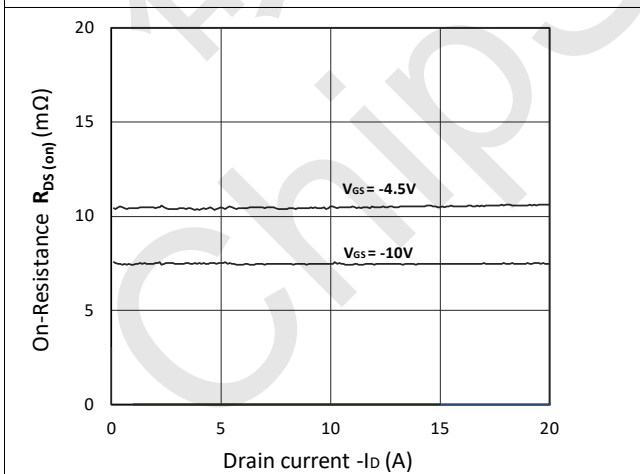


Figure 5.  $R_{DS(ON)}$  vs.  $I_D$

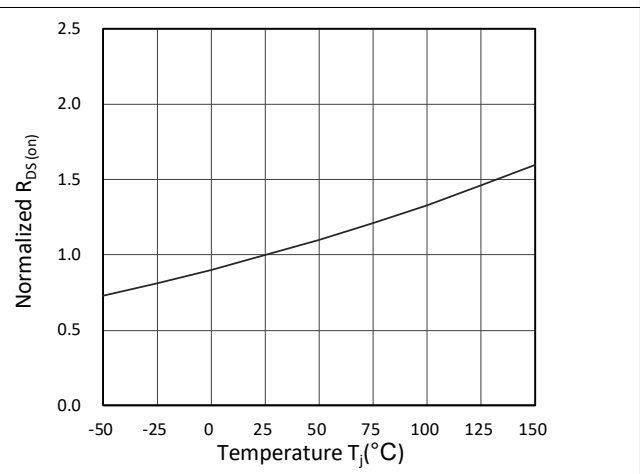


Figure 6. Normalized  $R_{DS(on)}$  vs. Temperature



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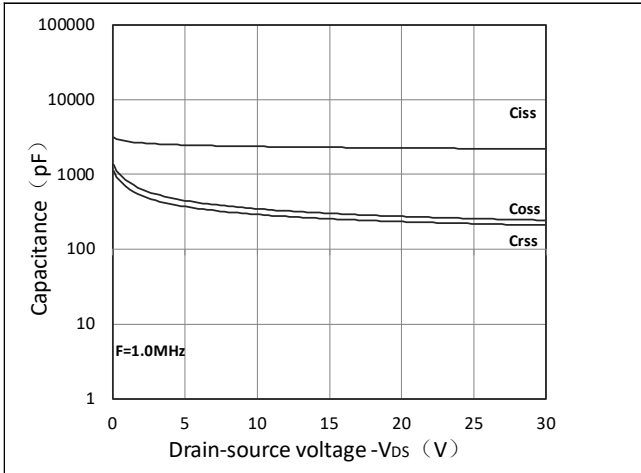


Figure 7. Capacitance Characteristics

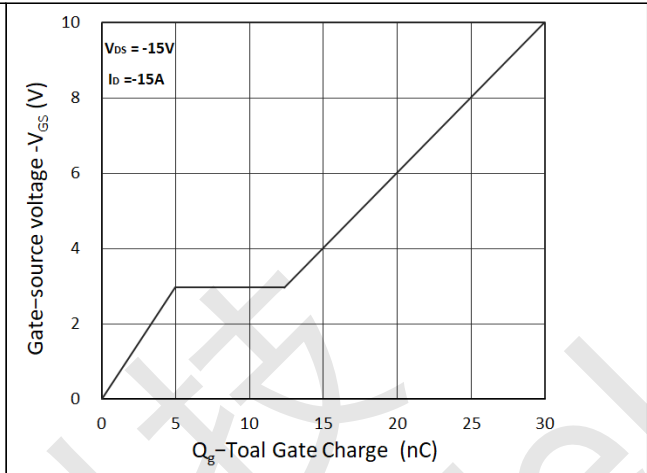


Figure 8. Gate Charge Characteristics

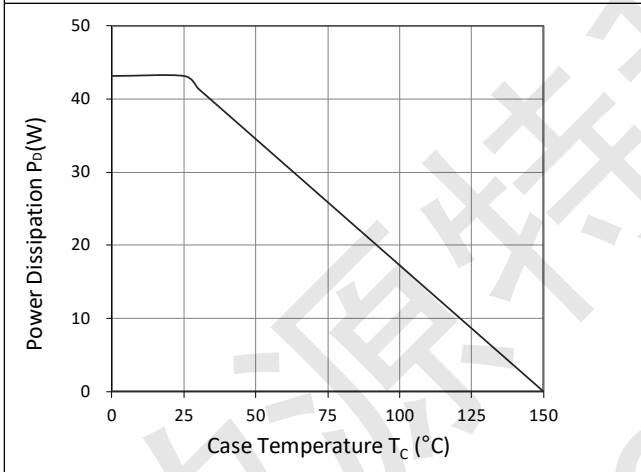


Figure 9. Power Dissipation

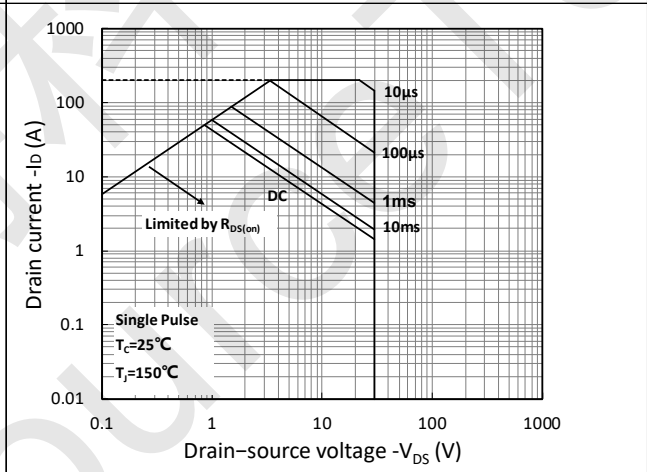


Figure 10. Safe Operating Area

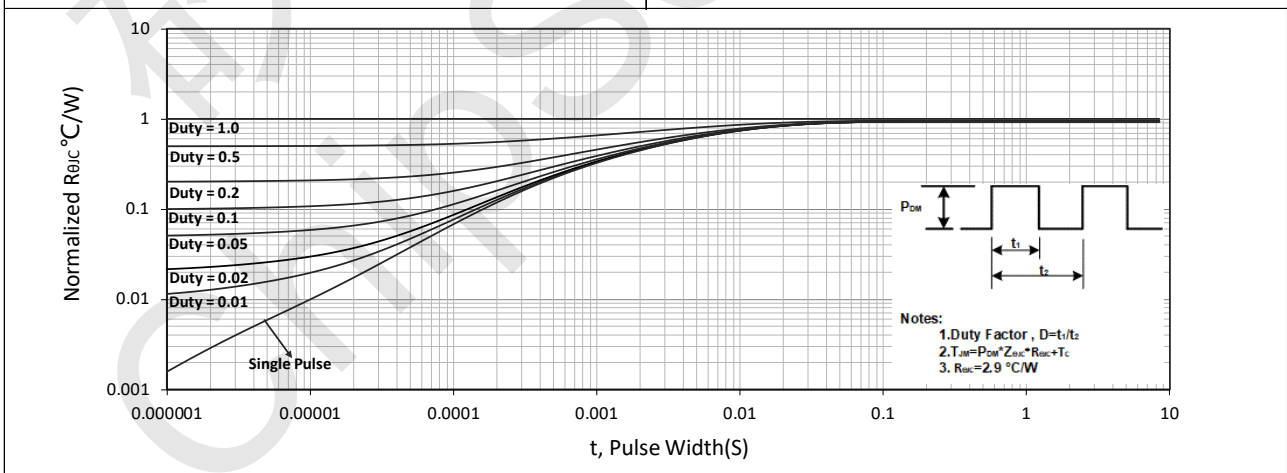
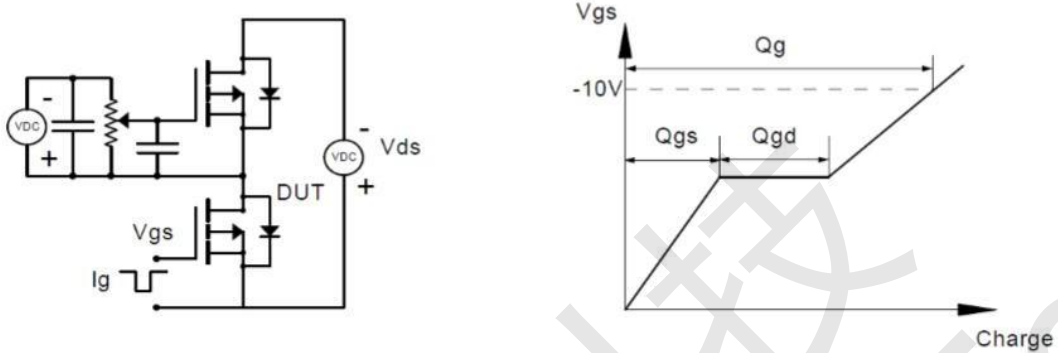


Figure 11. Normalized Maximum Transient Thermal Impedance

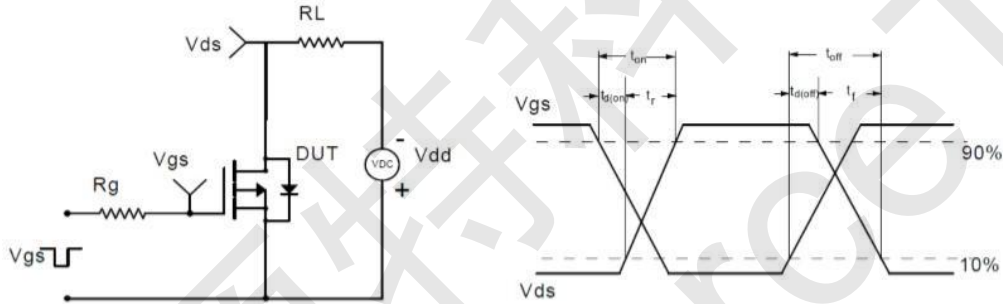


### CST60P03 Test Circuit

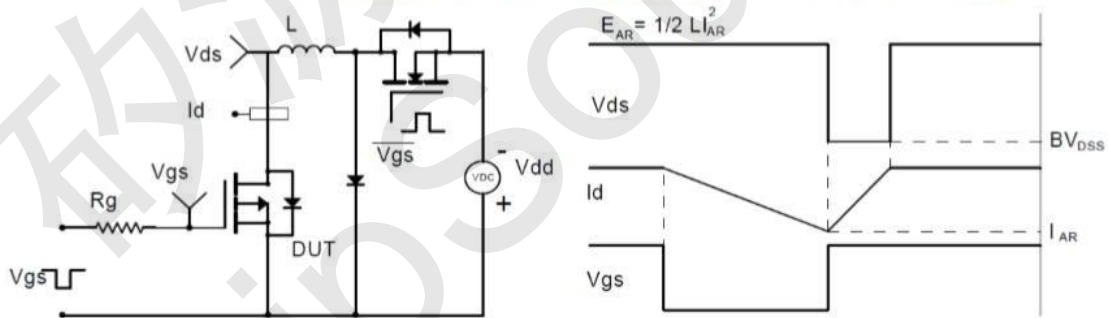
Gate Charge Test Circuit & Waveform



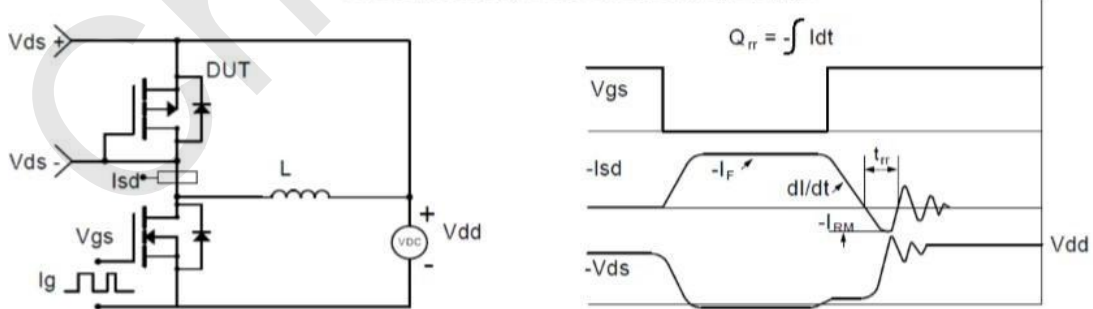
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

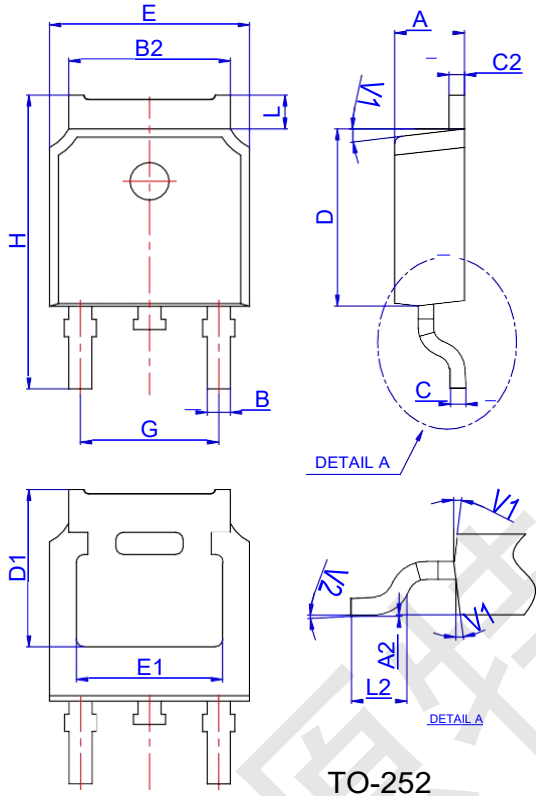


Diode Recovery Test Circuit & Waveforms



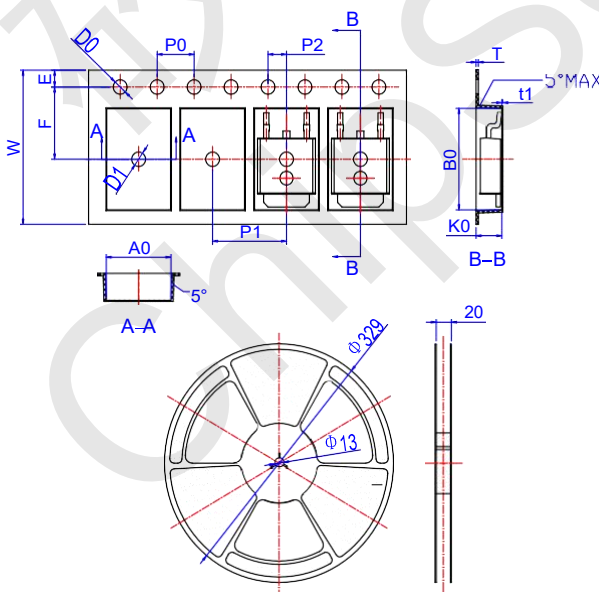


#### CST60P03 Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°		0°	6°

#### CST60P03 Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583